

Semiconductors
High-reliability discrete products and engineering services since 1977

## 2N5050-2N5052

## NPN SILICON HIGH POWER TRANSISTORS

## NFEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

| Ratings | Symbol | 2N5050 | 2N5051 | 2N5052 | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Voltage | $V_{\text {ceo }}$ | 125 | 150 | 200 | Vdc |
| Collector-Base Voltage | $\mathrm{V}_{\text {сво }}$ | 125 | 150 | 200 | Vdc |
| Emitter-Base Voltage | $\mathrm{V}_{\text {Ebo }}$ |  | 7.0 |  | Vdc |
| Collector Current | Ic |  | 2.0 |  | Adc |
| Total Power Dissipation $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | PD |  | 40 |  | W |
| Junction Temperature | TJ |  | 150 |  | ${ }^{\circ} \mathrm{C}$ |
| Storage Junction Temperature Range | $\mathrm{T}_{\text {stg }}$ |  | -65 to +200 |  | ${ }^{\circ} \mathrm{C}$ |
| Maximum Thermal Resistance Junction to Case | $\mathrm{R}_{\text {өлс }}$ |  | 7.0 |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

ELECTRICAL CHARACTERSITICS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Characteristics |  | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |
| Collector-Emitter Sustaining Voltage $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0$ | $\begin{aligned} & \text { 2N5050 } \\ & \text { 2N5051 } \\ & \text { 2N5052 } \end{aligned}$ | $V_{\text {ceo(sus) }}$ | $\begin{aligned} & 125 \\ & 150 \\ & 200 \end{aligned}$ |  | Vdc |
| Collector-Emitter Saturation Voltage $\mathrm{I}_{\mathrm{C}}=2 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=-0.5 \mathrm{Adc}$ |  | $\mathrm{V}_{\text {CE(sat) }}$ | - | 1.2 | Vdc |
| Collector-Base Saturation Voltage $\mathrm{I}_{\mathrm{C}}=2 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=-0.5 \mathrm{Adc}$ |  | $\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ | - | 1.5 | Vdc |
| Base-Emitter On-Voltage $\mathrm{Ic}=750 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=5 \mathrm{Vdc}$ |  | $\mathrm{V}_{\text {be(on) }}$ | - | 1.2 | Vdc |
| Collector Cutoff Current $\begin{aligned} & \mathrm{V}_{\mathrm{CE}}=125 \mathrm{Vdc}, \mathrm{I}_{\mathrm{B}}=0 \\ & \mathrm{~V}_{\mathrm{CE}}=150 \mathrm{Vdc}, \mathrm{I}_{\mathrm{B}}=0 \\ & \mathrm{~V}_{\mathrm{CE}}=200 \mathrm{Vdc}, \mathrm{I}_{\mathrm{B}}=0 \end{aligned}$ | $\begin{aligned} & \text { 2N5050 } \\ & \text { 2N5051 } \\ & \text { 2N5052 } \end{aligned}$ | Iceo |  | $5.0$ | mAdc |
| Collector Cutoff Current $V_{C B}=\text { Rated } V_{C B O}, I_{E}=0$ |  | $I_{\text {cbo }}$ | - | 0.1 | mAdc |
| Emitter Cutoff Current $\mathrm{V}_{\mathrm{EB}}=7 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0$ |  | Iebo | - | 1.0 | mAdc |
| DC Current Gain $\mathrm{I}_{\mathrm{C}}=750 \mathrm{mAdc}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}$ |  | $h_{\text {fe }}$ | 25 | 100 | - |
| Transition Frequency $\mathrm{Ic}=500 \mathrm{mAdc}, \mathrm{~V}_{\mathrm{CE}}=10 \mathrm{Vdc}, \mathrm{f}=1 \mathrm{MHz}$ |  | $\mathrm{f}_{\text {T }}$ |  |  | MHz |



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## MECHANICAL CHARACTERISTICS

| Case | TO-66 |
| :--- | :--- |
| Marking | Alpha-numeric |
| Polarity | See below |


| Dim | TO-66 |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Inches |  | Millimeters |  |
|  | Min | Max | Min | Max |
| BL | 1.205 | 1.280 | 30.60 | 32.50 |
| CD | 0.445 | 0.557 | 11.303 | 14.148 |
| CH | 0.257 | 0.284 | 6.540 | 7.220 |
| LL | 0.374 | 0.413 | 9.500 | 10.50 |
| BW | 0.680 | 0.727 | 17.26 | 18.46 |
| LD | 0.030 | 0.036 | 0.760 | 0.920 |
| HT | 0.054 | 0.065 | 1.380 | 1.650 |
| MHS | 0.951 | 0.976 | 24.16 | 24.78 |
| S1 | 0.545 | 0.614 | 13.84 | 15.60 |
| HD | 0.131 | 0.154 | 3.320 | 3.920 |
| PS | 0.191 | 0.210 | 4.860 | 5.340 |

